# mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

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### Silicon Bridge Rectifier

#### Features

#### • Plastic package has Underwriters Laboratory Flammability Classification 94V-0

- Types up to 1000 V  $V_{\text{RRM}}$
- · Ideal for printed circuit board
- High surge overload rating
- $\bullet$  High temperature soldering guaranteed: 260  $^{\rm 0}{\rm C}/$  10 seconds, 0.375(9.5mm) lead length
- Glass passivated chip junction
- High case dielectric strength 1500  $V_{RMS}$

#### **Mechanical Data**

Case: Molded plastic body over passivated junctions Mounting position: Any Terminals: Plated leads, solderable per MIL-STD-750 Method 2026 guaranteed

## **GBU6A thru GBU6G**

#### V<sub>RRM</sub> = 50 V - 1000 V I<sub>F</sub> =6 A

GBU	Package



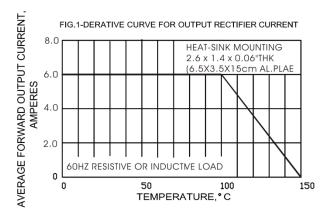
Parameter	Symbol	Conditions	GBU6A	GBU6B	GBU6D	GBU6G	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>		50	100	200	400	V
RMS reverse voltage	V <sub>RMS</sub>		35	70	140	280	V
DC blocking voltage	$V_{DC}$		50	100	200	400	V
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> ≤ 100 °C	6	6	6	6	А
Surge non-repetitive forward current, Half Sine Wave	I <sub>F,SM</sub>	T <sub>C</sub> = 25 °C, t <sub>p</sub> = 8.3 ms	175	175	175	175	А
Operating temperature	Tj		-55 to 150	-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T <sub>stg</sub>		-55 to 150	-55 to 150	-55 to 150	-55 to 150	°C

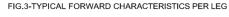
#### Electrical characteristics, at Tj = 25 °C, unless otherwise specified

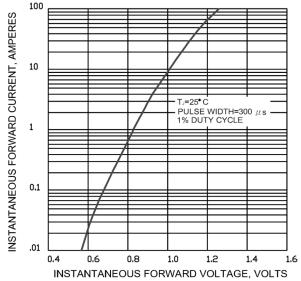
Parameter	Symbol	Conditions	GBU6A	GBU6B	GBU6D	GBU6G	Unit
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A, T <sub>j</sub> = 25 °C	1.1	1.1	1.1	1.1	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 50 V, T <sub>j</sub> = 25 °C	5	5	5	5	μA
		V <sub>R</sub> = 50 V, T <sub>j</sub> = 125 °C	500	500	500	500	
Thermal characteristics							
Thermal resistance, junction - case	$R_{thJA}$		7.4	7.4	7.4	7.4	°C/W
	$R_{thJL}$		2.2	2.2	2.2	2.2	0/11

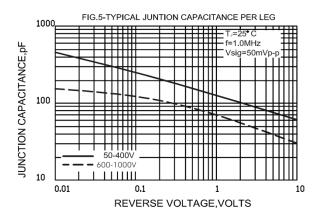


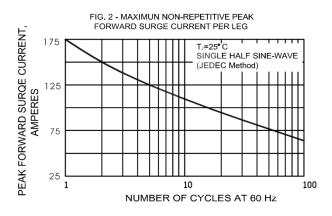
# **GBU6A thru GBU6G**

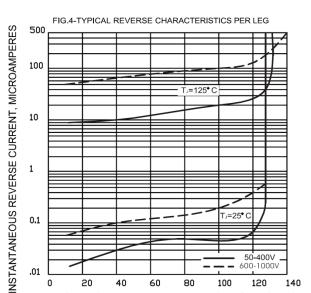


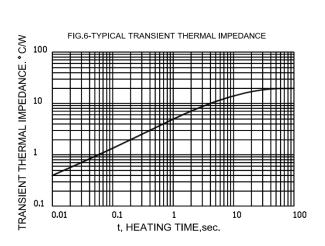












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